

<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>	Application No.	10/568,227
	Filing Date	May 17, 2006
	First Named Inventor	Vivian Alberts
	Art Unit	2895
(Multiple sheets used when necessary)	Examiner	Singal, Ankush K.
SHEET 1 OF 1	Attorney Docket No.	DMKISCH.002APC

U.S. PATENT DOCUMENTS					
Examiner Initials	Cite No.	Document Number Number - Kind Code (if known) Example: 1,234,567 B1	Publication Date MM-DD-YYYY	Name of Patentee or Applicant	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear

FOREIGN PATENT DOCUMENTS						
Examiner Initials	Cite No.	Foreign Patent Document Country Code-Number-Kind Code Example: JP 1234567 A1	Publication Date MM-DD-YYYY	Name of Patentee or Applicant	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear	T <sup>1</sup>

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>1</sup>
	1	V. Alberts, J. H. Schön, and E. Bucher, <i>Journal of Appl. Phys.</i> , 84(12), 1998, 6881-6885, "Improved material properties of polycrystalline CuInSe <sub>2</sub> prepared by rapid thermal treatment of metallic alloys in H <sub>2</sub> Se/Ar."	
	2	J. Palm, V. Probst, W. Stetter et al., <i>Thin Solid Films</i> , 451-452 (2004) 544-551, "CISSSe thin film PV modules: from fundamental investigations to advanced performance and stability."	
	3	M. Marudachalam, H. Hichri, R. Klenk, R.W. Birkmire, W.N. Schfarman and J. M. Schultz, <i>Appl. Phys. Lett.</i> 67(26), 1995, 3978, "Preparation of homogeneous Cu(InGa)Se <sub>2</sub> films by selenization of metal precursors in H <sub>2</sub> Se atmosphere."	
	4	K. Kushiya, M. Tachiyuki, T. Kase, I. Sugiyama, Y. Nagoya, D. Okumura, M. Satoh, O. Yamase and H. Takeshita <i>Sol. Energy Mater. Sol. Cells</i> 49, 1997, 277, "Fabrication of graded band-gap Cu(InGa)Se <sub>2</sub> thin-film mini-modules with a Zn(O,S,OH) <sub>x</sub> buffer layer."	
	5	I. M. Kötschau, H. Kerber, H. Wiesner, G. Hanna and H. W. Schock, Proceedings of the 16 <sup>th</sup> European Photovoltaic Solar Energy Conference, 1-5 May 2000, Glasgow, UK, pp. 724-727, "Band Gap Grading in Cu(In,Ga)(S,Se) <sub>2</sub> - based solar cells."	
	6	R. Gay, M. Dietrich, C. Fredric, C. Jensen, K. Knappm, D. Tarrant and D. Willett, "Efficiency and process improvements in CuInSe <sub>2</sub> -based modules" Proceedings of the international conference on E. C. Photovoltaic Solar Energy, Vol. 12 (1), 1994, 935-938.	
	7	T. Nakada, H. Ohbo, T. Wawtanabe, H. Nakazawa, M. Matsui and A. Kunioka, <i>Solar Energy Materials and Solar Cells</i> 49, 1997, 285, "Improved Cu(In,Ga)(S,Se) <sub>2</sub> thin film solar cells by solar sulfurization."	
	8	A. Gupta and S. Isomura, <i>Sol. Energy Mater. Sol Cells</i> 53, 1998, 385, "Precursor modification for preparation of CIS films by selenization technique."	

6212161  
110708

Examiner Signature	/Matthew Reames/	Date Considered	04/09/2009
--------------------	------------------	-----------------	------------

\***Examiner:** Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

T<sup>1</sup> - Place a checkmark in this area when an English language translation is attached.

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /M.R./